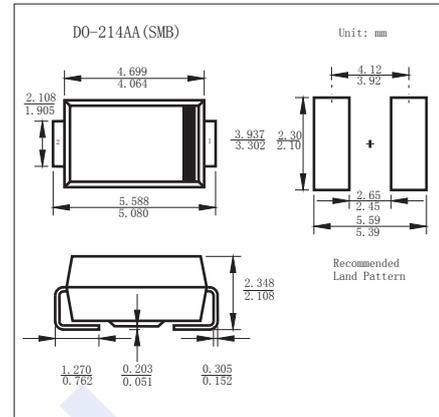


Schottky Diodes

SS32 THRU SS310

■ Features

- For surface mounted applications.
- Low profile package.
- Metal silicon junction, majority carrier conduction.
- Low power loss, high efficiency.
- High current capability, low forward voltage drop.
- High surge capability.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	SS32	SS33	SS34	SS35	SS36	SS38	SS39	SS310	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	90	100	V
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	63	70	
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	90	100	
Maximum average forward rectified current	I _{AV}	3								A
Peak forward surge current	I _{FSM}	70								
Maximum instantaneous forward voltage *1	V _F	0.55		0.7		0.85				V
Maximum instantaneous reverse current at rated DC blocking voltage Ta = 25°C *1 Ta = 70°C *1	I _R	0.5								mA
		20		10						
Typical Junction capacitance *2	C _J	500		300						pF
Thermal Resistance Junction to Ambient *3	R _{θJA}	55								°C/W
Junction Temperature	T _J	-65 to 125		-65 to 150						°C
Storage temperature range	T _{stg}	-65 to 150								

*1. Pulse test: 300μS pulse width, 1% duty cycle.

*2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

*3. P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas.

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■ Typical Characteristics

